

| Form PTO-1449 (Rev. 8-83) | | U.S. Department of Commerce Patent and Trademark Office | | Attorney Docket No. 0756-1936 | Serial No. Not Yet Assigned | |
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| INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary) | | Applicant: Shunpei YAMAZAKI et al. | | | PTO 510 55777 U.S. 02/23/99 | |
| | | Filing Date: February 23, 1999 | | Group: 2812 | | |
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| Examiner | <i>Richard A. H.</i> | | Date Considered 2/24/00 | | | |
| *EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | | | | | | |

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| Examiner | <i>John Doe</i> | | Date Considered | <i>2/24/00</i> | | |